

INFORMATION DISCLOSURE STATEMENT BY APPLICANT				<i>Complete if Known</i>	
				Application Number	New Application 10/584882
				Filing Date	Herewith
				First Named Inventor	Fariba HATAMI et al
				Group Art Unit	10584882 - GAU: 2815
				Examiner Name	Jay C. Kim
				Confirmation No.	
Sheet	1	of	4	Attorney Docket Number	3367-103

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (If known)		
/J.K./	1.	6,984,850		Hiroshi Nakatsu	1/10/06
/J.K./	2.	6,936,858		Hiroshi Nakatsu†	8/30/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code. ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached. AB indicates that only an English language abstract is attached.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT				<i>Complete if Known</i>	
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ²
		Office ³ Code	Number ⁴	Kind ⁵ (if known)			
/J.K./	15.	JP	08335718 (abstract only)	A	Daido Steel Co., Ltd.	12/17/96	AB
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/J.K./	19.	WO	99/50916	A1	Massachusetts Institute...	10/7/99	
Examiner Signature	/Jay Kim/				Date Considered	03/11/2009	

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
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	28.	F. Hatami, W. T. Masselink, L. Schrottke, J. W. Tomm, V. Talalaev, C. Kristukat, and A. R. Goni: "InP quantum dots embedded in GaP: "Optical properties and carrier dynamics", Phys. Rev. B 67, 85306-14 (2003)	
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Examiner Signature	/Jay Kim/		Date Considered	03/11/2009

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